

## **GENERAL DESCRIPTION**

This series of surface mount PIN and Limiter diodes utilize new and unique monolithic MMSM technology. The technology is a package/device integration accomplished at the wafer fabrication level. Since the cathode and anode interconnections utilize precision photolithographic techniques rather than wire bonds, parasitic package inductance is tightly controlled. The package parasitics provide smooth non-resonant functionality through X Band. This series of devices meets RoHS requirements per EU Directive 2002/95/EC.

## **APPLICATIONS**

The MPP4200 series of PIN diodes can be used in RF circuits as an on/off element, as a switch, or as a current controlled resistor in attenuators extending over the frequency range from UHF through X band. Switch applications include high speed switches (ECM systems), TR switches channel or antenna selection switches (Telcom and WLAN applications), duplexers (radar) and digital phase shifters (phased arrays). These diodes are also used as passive and active limiters for low to moderate RF power levels. Attenuator type applications include amplitude modulators, AGC attenuators and power levelers.

## **KEY FEATURES**

- Up to 10W incident RF power handling
- Low parasitics
- L<sub>P</sub> = 0.02nH Typical
- C<sub>P</sub> = 0.04pF Typical
- Broadband Performance through X-Band
- Available on Tape & Reel or on Film Frame for pick & place
- Small, SOD 323 Footprint
- RoHS Compliant <sup>1</sup>
- 1- These devices are supplied with gold terminations.

## **APPLICATION/BENEFITS**

- Receiver protection circuits
- Broadband Switching
- Economy Switching
- RF Attenuators
- MRI

#### ABSOLUTE MAXIMUM RATINGS @ 25°C

Rating	Symbol	Value	Unit
Maximum Leakage Current @80% of minimum Rated V <sub>B</sub>	I <sub>R</sub>	0.5	uA
Operating Temperature	TOP	-55 to +150	٥C
Storage Temperature	Tstg	-65 to +150	°C

For the most current data, consult MICROSEMI's website: **www.MICROSEMI.com** Specifications are subject to change, consult the RFIS factory at (978) 442-5600 for the latest information.



## **DEVICE ELECTRICAL PARAMETERS AT 25°C**

Model Number	Package Style	<b>V</b> <sub>B</sub> (V) I <sub>R</sub> =10μΑ <b>(Min)</b>	Ст(рF)¹ @-10∨ (Мах)	<b>R</b> s(Ω)² @0.01mA <b>(Typ)</b>	<b>R</b> s(Ω)² @1mA	<b>R</b> s(Ω)² @10mA <b>(Max)</b>	<b>R</b> s(Ω)² @20mA (Max)
MPP4201	206	70	0.20				2.5
MPP4202	206	50	0.15				2.8
MPP4203	206	50	0.10				3.0
MPP4204	206	25	0.15			2.0	
MPP4205	206	70	0.15	250	7-16	5.0	

Model Number	Package Style	Т∟ (Тур)	Application
MPP4201	206	150	Switching / Attenuation
MPP4202	206	50	Switching
MPP4203	206	50	Economy Switching
MPP4204	206	20	Switching
MPP4205	206	150	Attenuation

Notes:

1- Capacitance is measured at f = 1 MHz.

- Series Resistance (R<sub>s</sub>) is measured at f = 100 MHz. Devices are mounted in a package suitable for testing. 2-
  - a. R<sub>s</sub> is measured at 1 GHz for the MPL series devices.
    b. Not measured in anti-parallel configuration.
  - Vr = 0V. This value is the sum of two junctions. c.



#### TYPICAL RS VS If @ 25°C





#### PACKAGE STYLE 206



#### **Revision History**

Revision Level / Date	Para. Affected	Description
2 / 16 April 2013	-	Initial Release
3 / 21 October 2013	Applications / Device Electricals	Revised

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